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--21. The production method according to Claim 12, wherein the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion.--

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--22. The production method according to Claim 13, wherein the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion.--

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--23. A bonding wafer produced by the hydrogen ion delamination method, wherein a thin film formed on a base wafer is removed for a region of 1-5 mm from a peripheral end of the base wafer.--

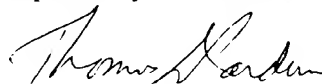
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--24. The bonding wafer according to Claim 23, wherein the thin film has an SOI layer and at least the SOI layer is removed for a region of 1-5 mm from the peripheral end of the base wafer.--

REMARKS

Claims 10-24 are pending. Claims 1-9 are cancelled and claims 10-24 are added.

Prompt and favorable consideration on the merits is respectfully requested.

Respectfully submitted,



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